

isc Silicon NPN Power Transistor

2SC6093

DESCRIPTION

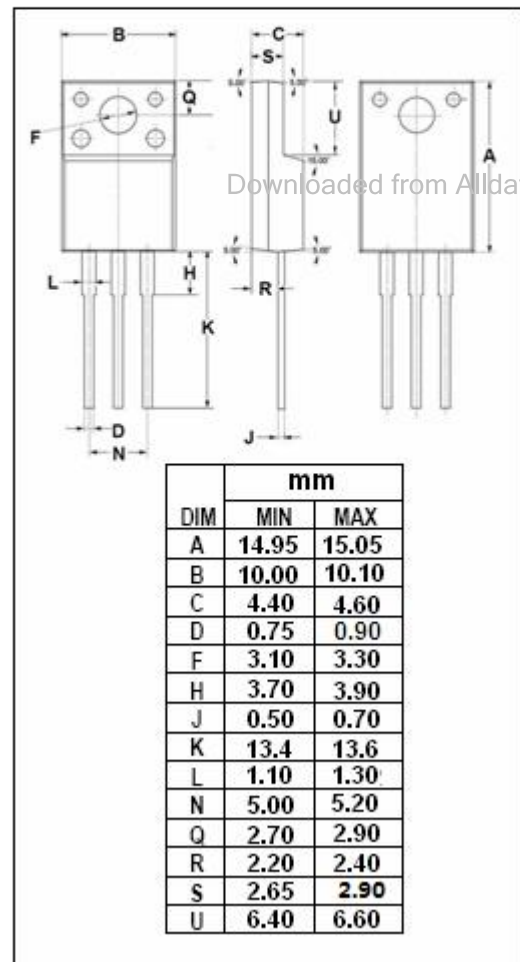
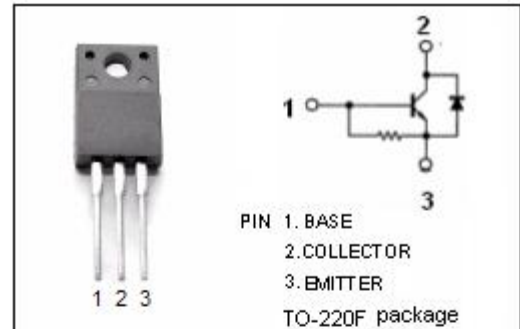
- Low saturation voltage
- Built-in damper diode type
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for high voltage color display horizontal deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	1500	V
V_{CEO}	Collector-Emitter Voltage	800	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current- Continuous	5	A
I_B	Base Current- Continuous	2	A
I_{CP}	Collector Current-Pulse	12	A
P_C	Collector Power Dissipation @ $T_a=25^{\circ}\text{C}$	2	W
	Collector Power Dissipation @ $T_c=25^{\circ}\text{C}$	25	
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^{\circ}\text{C}$



isc Silicon NPN Power Transistor**2SC6093****ELECTRICAL CHARACTERISTICS** $T_c=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CE(sat)-1}$	Collector-Emitter Saturation Voltage	$I_C = 1.35\text{A}; I_B = 0.27\text{A}$	0.1		0.3	V
$V_{CE(sat)-2}$	Collector-Emitter Saturation Voltage	$I_C = 2.7\text{A}; I_B = 0.54\text{A}$			2.0	V
$V_{BE(sat)}$	Base-Emitter Saturation Voltage	$I_C = 2.7\text{A}; I_B = 0.54\text{A}$			1.5	V
I_{CBO}	Collector Cutoff Current	$V_{CB} = 800\text{V}; I_E = 0$			10	μA
I_{EBO}	Emitter Cutoff Current	$V_{EB} = 4\text{V}; I_C = 0$	40		130	mA
h_{FE-1}	DC Current Gain	$I_C = 0.5\text{A}; V_{CE} = 5\text{V}$	10			
h_{FE-2}	DC Current Gain	$I_C = 3\text{A}; V_{CE} = 5\text{V}$	5.3		7.5	